SOD523 40V LOW LEAKAGE SCHOTTKY BARRIER DIODE

SUMMARY

V_R = 40V; I_{FAV} = 650mA; V_F = 570mV typ @ 100mA; I_R = 1μA typ @ 30V

DESCRIPTION

Packaged in the SOD523 package this addition to the Zetex Low Leakage Schottky diode range offers an ideal low VF/IR performance combined with a low package height of 0.9mm making the device suitable for various converter, charger, and LED driver circuits.

FEATURES

- Low V_F
- 380mA continuous current rating
- Low profile SOD523 package (0.9mm)

APPLICATIONS

- DC DC converters
- Mobile telecomms
- Charger circuits
- LED driver circuits
- MOSFET voltage protection circuits

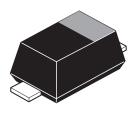
ORDERING INFORMATION

DEVICE	REEL SIZE	TAPE WIDTH	QUANTITY PER REEL
ZLLS350TA	7"	8mm embossed	3,000 units
ZLLS350TC	13"	8mm embossed	10,000 units

DEVICE MARKING

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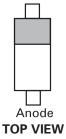
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SOD523



Cathode





ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT
Continuous reverse voltage	V _R	40	V
Continuous forward current	I _F	380	mA
Average peak forward current; D.C. = 50%	I _{FAV}	650	mA
Non repetitive forward current t $< 100 \mu S$	I _{FSM}	6.0	А
< 10mS		1.3	А
Power dissipation at T _A =25°C ^(a)	PD	357	mW
Power dissipation at $T_A=25^{\circ}C^{(b)}$	PD	413	mW
Operating and storage temperature range	T _{stg}	-55 to +150	°C
Junction temperature	Tj	150	°C

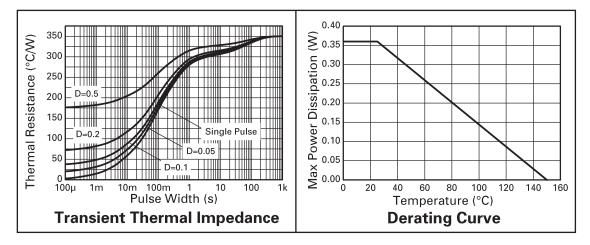
THERMAL RESISTANCE

PARAMETER	SYMBOL	LIMIT	UNIT
Junction to ambient ^(a)	$R_{\theta JA}$	350	°C/W
Junction to ambient ^(b)	$R_{\theta JA}$	303	°C/W

NOTES:

(a) For a single device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of 1oz copper in still air conditions. (b) As (a) above measured at t<5 secs.





CHARACTERISTICS

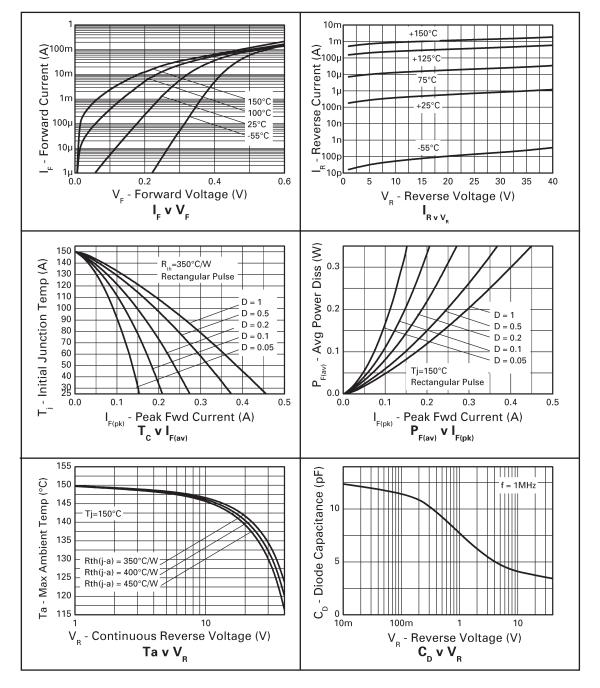


ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ unless otherwise stated)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS
Reverse breakdown voltage	V _{(BR)R}	40	63		V	I _R =100μA
Forward voltage	V _F		380	450	mV	I _F =30mA*
			425	520	mV	I _F =50mA*
			520	635	mV	I _F =100mA*
			780	1000	mV	I _F =275mA*
Reverse current	I _R		1	4	μA	V _R =30V
Diode capacitance	CD		3.5	6	pF	f=1MHz; V _R =30V
Reverse recovery time	t _{rr}		1		nS	Switched from
						I _F =100mA, to I _R =100mA
						Measured at I _R =10mA

* Measured under pulsed conditions. Pulse width $\leq 300 \mu s;$ duty cycle $\leq 2\%.$

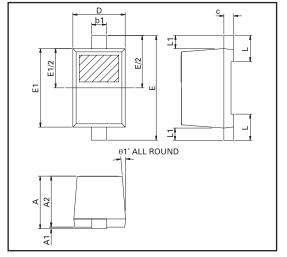




CHARACTERISTICS



PACKAGE OUTLINE



PACKAGE DIMENSIONS

DIM	Millin	neters	Inc	hes	DIM	Millim	neters	Inches	
DIIVI	Min	Max	Min	Max		Min	Max	Min	Max
А	-	0.800	-	0.0314	Е	1.500	1.700	0.0590	0.0669
A1	0.000	0.100	0.000	0.0039	E1	1.100	1.300	0.0433	0.0511
A2	0.600	0.800	0.0236	0.0314	L	0.200	0.400	0.0078	0.0157
b1	0.160	0.300	0.0062	0.0118	L1	0.170	0.230	0.0066	0.0090
с	0.080	0.220	0.0031	0.0086	θ1°	4°	10°	4°	10°
D	0.700	0.900	0.0275	0.0354					

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